

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s) : An L. STEEGEN et al. Confirmation No. 2905

Appln. No. : 10/605,906 Group Art Unit: 2813

Filed : November 5, 2003 Examiner: Stephen W. Smoot

For : METHOD AND STRUCTURE FOR FORMING STRAINED SI FOR CMOS DEVICES

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
U.S. Patent and Trademark Office
Customer Service Window, Mail Stop Amendment
Randolph Building
401 Dulany Street
Alexandria VA 22314

Sir :

In accordance with the duty of disclosure under 37 C.F.R. § 1.56 and supplemental to the Information Disclosure Statements filed on filed on November 5, 2003, August 23, 2005 and February 9, 2005, applicant respectfully brings the following documents, listed on the attached form PTO-1449, to the attention of the Examiner in charge of the above-identified application.

Further to the U.S. Patent and Trademark Office's decision to waive the requirement under 37 C.F.R. § 1.98 (a)(2)(i), copies of the U.S. patents and U.S. published patent applications are not enclosed herewith. However, if any copies are needed, the Examiner is respectfully requested to contact the undersigned. Copies of the non-US patent documents as well as the documents listed in the "Other Documents" section of the attached PTO-1449 are enclosed.

Applicant respectfully requests that the Examiner consider the materials cited and indicate such consideration by appropriately initialing the enclosed PTO-1449 Form and including a copy of the initialed form in the next official communication.

Applicants note that this Information Disclosure Statement is being after receipt of a first action on the merits from the U.S. Patent and Trademark Office. Accordingly, Applicants are herein submitting the required fee, and authorization is hereby given to charge Deposit Account No. 09-0458 any fee necessary to ensure consideration of these materials.

Should there be any questions concerning this application, the Examiner is invited to contact the undersigned at the below listed telephone number.

Respectfully submitted,
An L. STEEGEN et al.



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June 29, 2006
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FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. FIS920030236US1		Application No. 10/605,906	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Applicant An L. STEEGEN et al.					
		Filing Date 11/05/2003		Group 2813			
		U.S. PATENT DOCUMENTS					
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		US 2002/0063292 A1	5-30-2002	Armstrong et al.			
		US 2003/0032261 A1	2-13-2003	Yeh et al.			
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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
		JP 64-76755	3-22-1989	Japan			X
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER				DATE CONSIDERED			
*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No.		Application No.	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Applicant					
		Filing Date		Group			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
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		G. Zhang, et al., "A New 'Mixed-Mode' Reliability Degradation Mechanism in Advanced Si and SiGe Bipolar Transistors." IEEE Transactions on Electron Devices, vol. 49, no. 12, December 2002, pp. 2151-56.					
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EXAMINER			DATE CONSIDERED				
*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							